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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

HITOSHI KATO, ET AL. : EXAMINER: HARRISON, M. D.

SERIAL NO: 10/518,025 :

FILED: DECEMBER 15, 2004 : GROUP ART UNIT: 2813

FOR: METHOD OF CVD FOR FORMING
SILICON NITRIDE FILM ON
SUBSTRATE

AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Responsive to the Office Action dated September 19, 2005, Applicants respectfully request reconsideration of the above-identified application in view of the following amendment and remarks.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Discussion of the Amendment begins on page 6 of this paper.

Remarks begin on page 7 of this paper.